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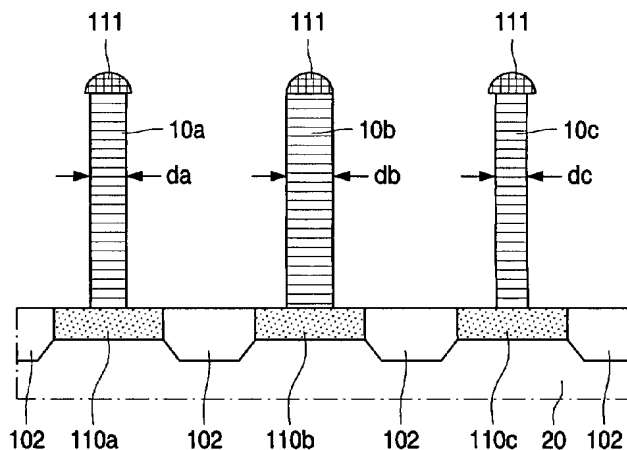
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(54) Title: FABRICATING A SET OF SEMICONDUCTING NANOWIRES, AND ELECTRIC DEVICE COMPRISING A SET  
OF NANOWIRES



(57) Abstract: The method of fabricating a set of semiconducting nanowires (10) having a desired wire diameter (d) comprises the steps of providing a set of pre-fabricated semiconducting nanowires (10'), at least one pre-fabricated semiconducting nanowire having a wire diameter (d') larger than the desired wire diameter (d), and reducing the wire diameter of the at least one pre-fabricated nanowire (10') by etching, the etching being induced by light which is absorbed by the at least one pre-fabricated nanowire (10'), a spectrum of the light being chosen such that the absorption of the at least one pre-fabricated nanowire being significantly reduced when the at least one pre-fabricated nanowire reaches the desired wire diameter (d). The electric device (100) may comprise a set of nanowires (10) having the desired wire diameter (d). The apparatus (29) may be used to execute the method according to the invention.

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